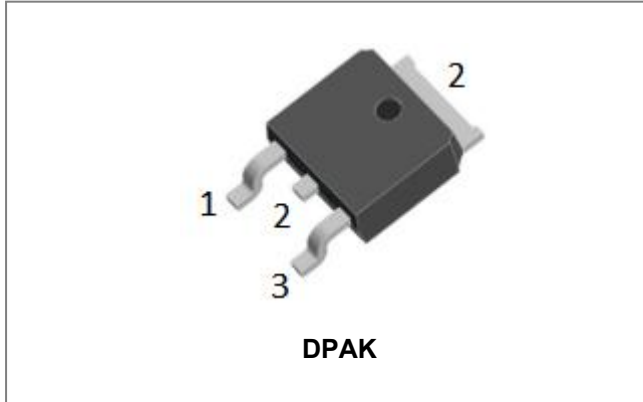


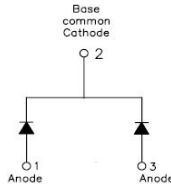
MBRD630CT SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- “-A” is an AEC-Q101 qualified device
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

Maximum Ratings (limiting values, T_C = 25°C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	30	V
Average Rectified Forward Current	I _{F(AV)}	T _C =147°C, In DC	3(peg leg)	A
			6(peg device)	
Peak One Cycle Non-Repetitive Surge Current(peg leg)	I _{FSM}	8.3 ms, half Sine pulse	75	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (per leg) *	V _{F1}	@ 3 A, Pulse, T _J = 25 °C	0.46	0.70	V
		@ 6 A, Pulse, T _J = 25 °C	0.52	0.90	
Reverse Current (per leg) *	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.01	0.1	mA
		@V _R = rated V _R , T _J = 125 °C	5	50	
Junction Capacitance(per leg)	C _T	@V _R = 5V, T _C = 25 °C, f _{SIG} = 1MHz	220	220	pF

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to + 150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	-	1.6	$^{\circ}\text{C/W}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta\text{JA}}$	-	85	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

Ratings and Characteristics Curves

Figure 1 Typical Forward Characteristics

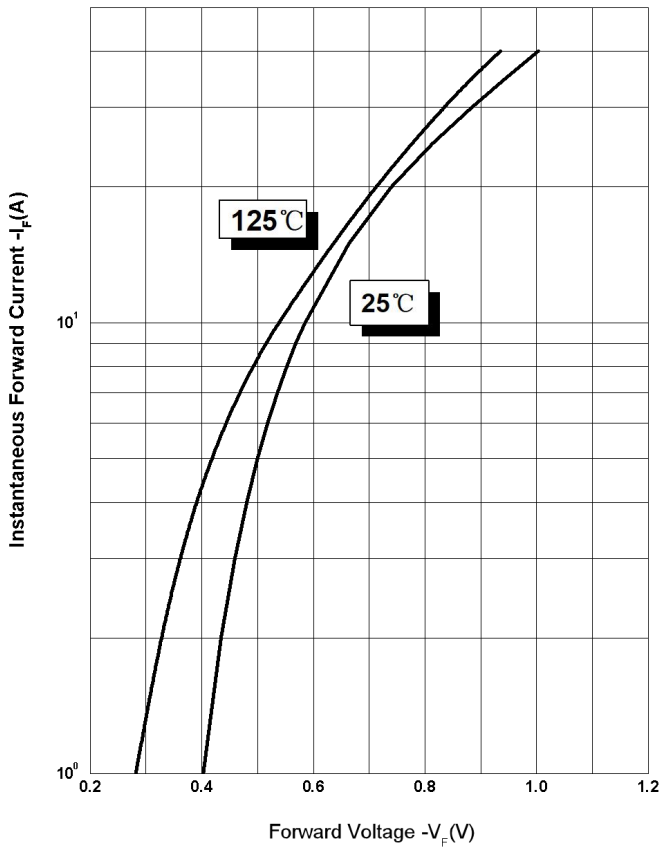


Figure 2 Typical Reverse Characteristics

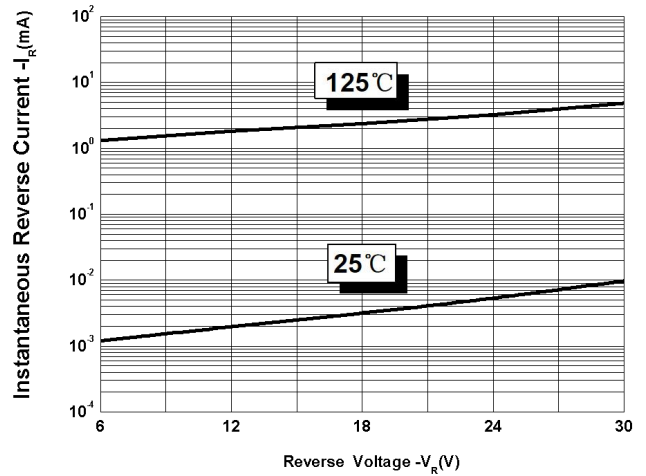
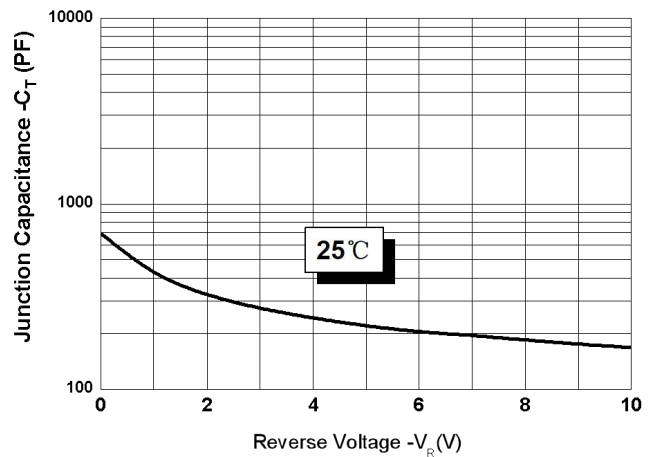
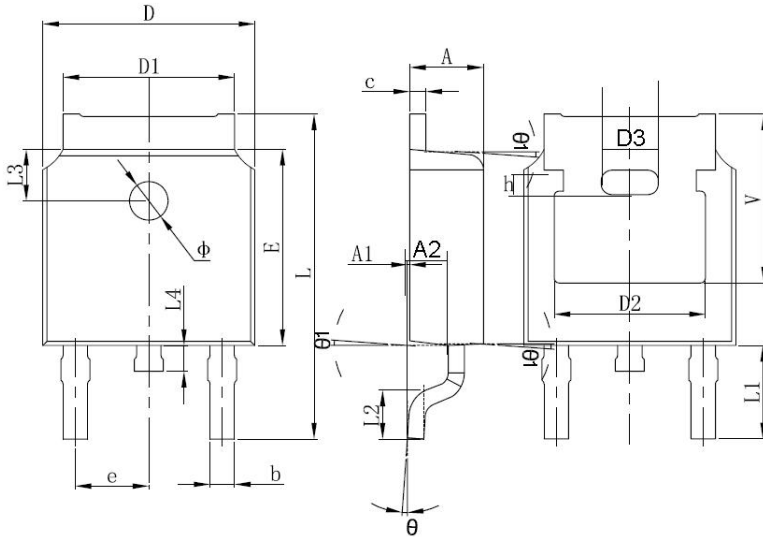


Figure 3 Typical Junction Capacitance



Mechanical Dimensions DPAK



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	2.18	-	2.39
A1	-	-	0.13
b	0.64	-	0.89
c	0.46	-	0.89
D	6.35	-	6.73
D1	4.95	-	5.46
D2	4.32	-	-
E	5.97	6.1	6.22
e	2.29BSC		
L	9.4	-	10.41
L1	2.90 REF.		
L2	1.4	1.52	1.78
L3	1.60 REF.		
L4	-	-	1.02
Φ	1.1	-	1.3
Θ	0°	-	10°
V	5.21	-	-

The outline from different package houses may have slight differences. So the outline above is just schematic. The dimensions are controlled per specifications.

Ordering Information

Device	Package	Shipping
MBRD630CT	DPAK (Pb-Free)	2500pcs / reel
MBRD630CTTR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

Marking Diagram

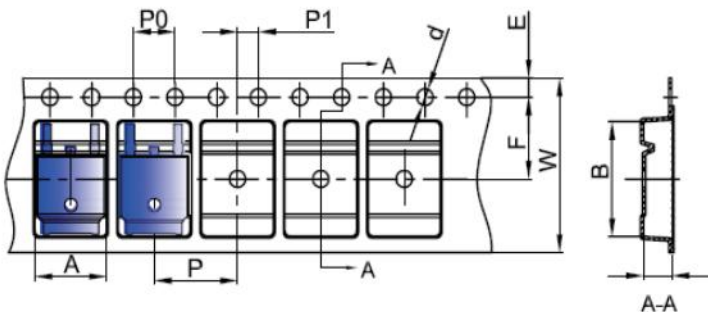


Where XXXXX is YYWWL

- MBR = Device Type
- D = Package type
- 6 = Forward Current (6A)
- 30 = Reverse Voltage (30V)
- CT = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification DPAK



SYMBOL	Millimeters	
	Min.	Max.
A	6.80	7.00
B	10.40	10.60
C	2.60	2.80
d	Φ1.45	Φ1.65
E	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
P	7.90	8.10
P1	1.90	2.10
W	15.90	16.30

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